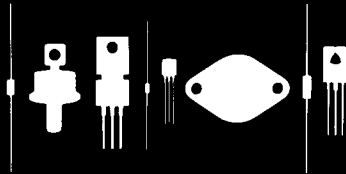


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MJE341
MJE344
NPN SILICON
POWER TRANSISTOR
JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE341, MJE344 types are NPN Silicon Power Transistors designed for amplifier applications requiring high f_T .

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

	SYMBOL	MJE341	MJE344	UNITS
Collector-Base Voltage	V_{CBO}	175	200	V
Collector-Emitter Voltage	V_{CEO}	150	200	V
Emitter-Base Voltage	V_{EBO}	3.0	5.0	V
Continuous Collector Current	I_C	500		mA
Continuous Base Current	I_B	250		mA
Power Dissipation	P_D	20		W
Operating and Storage				
Junction Temperature	T_J, T_{stg}	-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JC}	6.25		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MJE341		MJE344		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB} = \text{Rated } V_{CBO}$		0.3		0.1	mA
I_{CEO}	$V_{CE} = \text{Rated } V_{CEO}$		1.0		1.0	mA
I_{EBO}	$V_{EB} = \text{Rated } V_{EBO}$		0.1		0.1	mA
BV_{CEO}	$I_C = 1.0\text{mA}$	150		200		V
$V_{CE(SAT)}$	$I_C = 50\text{mA}, I_B = 5.0\text{mA}$		-		1.0	V
$V_{CE(SAT)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$		2.3		-	V
$V_{BE(ON)}$	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$		1.0		1.0	V
h_{FE}	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	20		-		
h_{FE}	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	25	200	30	300	
h_{FE}	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	20		-		
f_T	$V_{CE} = 25\text{V}, I_C = 50\text{mA}, f = 10\text{MHz}$	15		15		MHz
C_{ob}	$V_{CB} = 20\text{V}, I_E = 0, f = 100\text{kHz}$		15		15	pF
h_{fe}	$V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 1.0\text{kHz}$	25		25		